

NX8315XC

1 310 nm FOR LONG HAUL 2.5 Gb/s IngaAsP MQW-DFB LASER DIODE TOSA

DESCRIPTION

The NX8315XC is a 1 310 nm Multiple Quantum Well (MQW) structured Distributed Feed-Back (DFB) laser diode TOSA (transmitter optical sub-assembly) with InGaAs monitor PIN-PD in a receptacle type package designed for SFF/SFP transceiver with LC duplex receptacle.

APPLICATION

• STM-16 (L-16.1), SONET OC-48 (LR-1)

FEATURES

· Internal optical isolator

Optical output power
 Pf = 2.0 mW

Low threshold current
 Ith = 10 mA TYP. @ Tc = 25°C

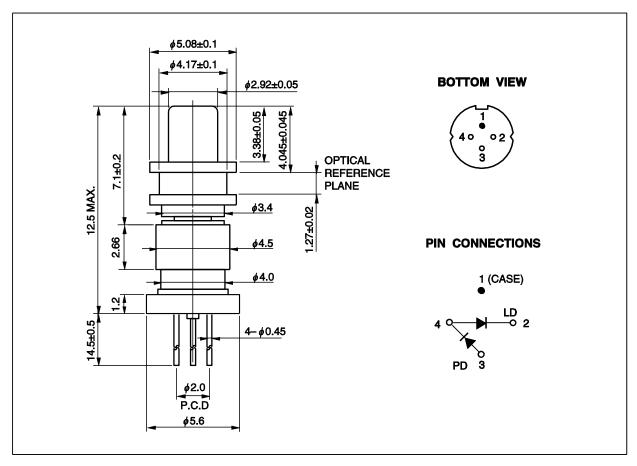
• Wide operating temperature range $Tc = -40 \text{ to } +85^{\circ}\text{C}$

InGaAs monitor PIN-PD



The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

PACKAGE DIMENSIONS (UNIT: mm)



ORDERING INFORMATION

Part Number	Package	Pin Connections
NX8315XC-AZ	ϕ 5.6 mm TOSA	19 € 50 19 € 10 19 € 10 10 10 10 10 10 10 10 10 10 10 10 10 1

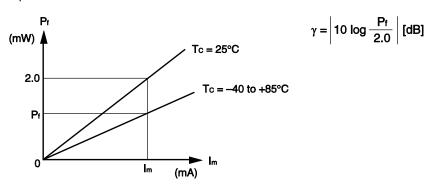
ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Ratings	Unit
Optical Output Power from Fiber	Pf	5.0	mW
Forward Current of LD	lF	150	mA
Reverse Voltage of LD	VR	2.0	V
Forward Current of PD	lF	2.0	mA
Reverse Voltage of PD	VR	15	V
Operating Case Temperature	Tc	-40 to +85	°C
Storage Temperature	Tstg	-40 to +85	°C
Lead Soldering Temperature	Tsld	350 (3 sec.)	°C

ELECTRO-OPTICAL CHARACTERISTICS (Tc = -40 to +85°C, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Optical Output Power from Fiber	Pf	cw		2.0		mW
Operating Voltage	Vop	CW, P _f = 2.0 mW		1.2	1.8	V
Threshold Current	Ith	CW	2		50	mA
		CW, Tc = 25°C	4	10	20	
Differential Efficiency	η d	CW, P _f = 2.0 mW	0.04		0.29	W/A
		CW, P _f = 2.0 mW, T _C = 25°C	0.07	0.10	0.20	
Peak Emission Wavelength	λp	CW, P _f = 2.0 mW, RMS (-20 dB)	1 280		1 335	nm
Side Mode Suppression Ratio	SMSR	CW, P _f = 2.0 mW	30			dB
Rise Time	tr	Ib = Ith, 10-90%			150	ps
Fall Time	t _f	Ib = Ith, 90-10%			150	ps
Monitor Current	Im	CW, V _R = 1.5 V, P _f = 1.0 mW	70		1 000	μΑ
Monitor Dark Current	lo	V _R = 1.5 V			500	nA
		VR = 1.5 V, Tc = 25°C			50	
Tracking Error*1	γ	CW, I _m = const. (@ P _f = 2.0 mW)	-1.5		1.5	dB
Repeatability	_	With master pigtail	-1.0		1.0	dB
Optical Isolation	ls	CW, P _f = 2.0 mW	20			dB

*1 Tracking Error: γ



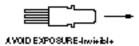
REFERENCE

Document Name	Document No.	
Opto-Electronics Devices Pamphlet	PX10160E	

SAFETY INFORMATION ON THIS PRODUCT



SEMICONDUCTOR LASER



Lever Redission is emitted from this aperture

Warning Laser Beam	A laser beam is emitted from this diode during operation. The laser beam, visible or invisible, directly or indirectly, may cause injury to the eye or loss of eyesight. • Do not look directly into the laser beam.
	Avoid exposure to the laser beam, any reflected or collimated beam.
Caution GaAs Products	This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.
	Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
	Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
	Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
	Do not burn, destroy, cut, crush, or chemically dissolve the product.
	Do not lick the product or in any way allow it to enter the mouth.
Caution Optical Fiber	A glass-fiber is attached on the product. Handle with care. When the fiber is broken or damaged, handle carefully to avoid injury from the damaged part or fragments.